Advanced damage free neutral beam etching technology for the application of broad band optical light trapping in thin Si (<100 μm) wafer based Solar cells

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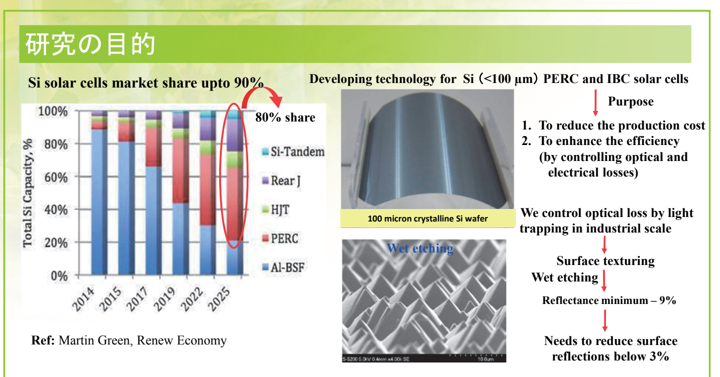

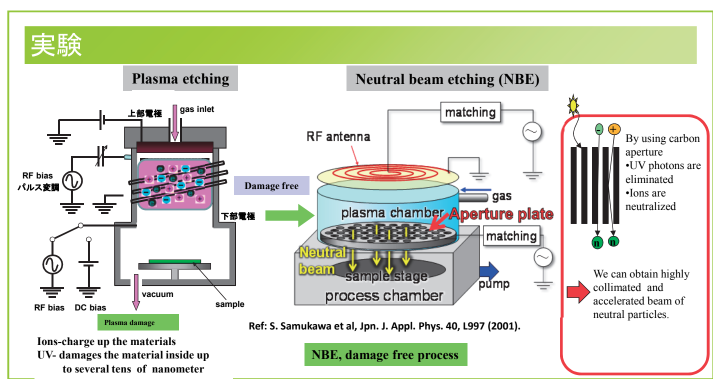

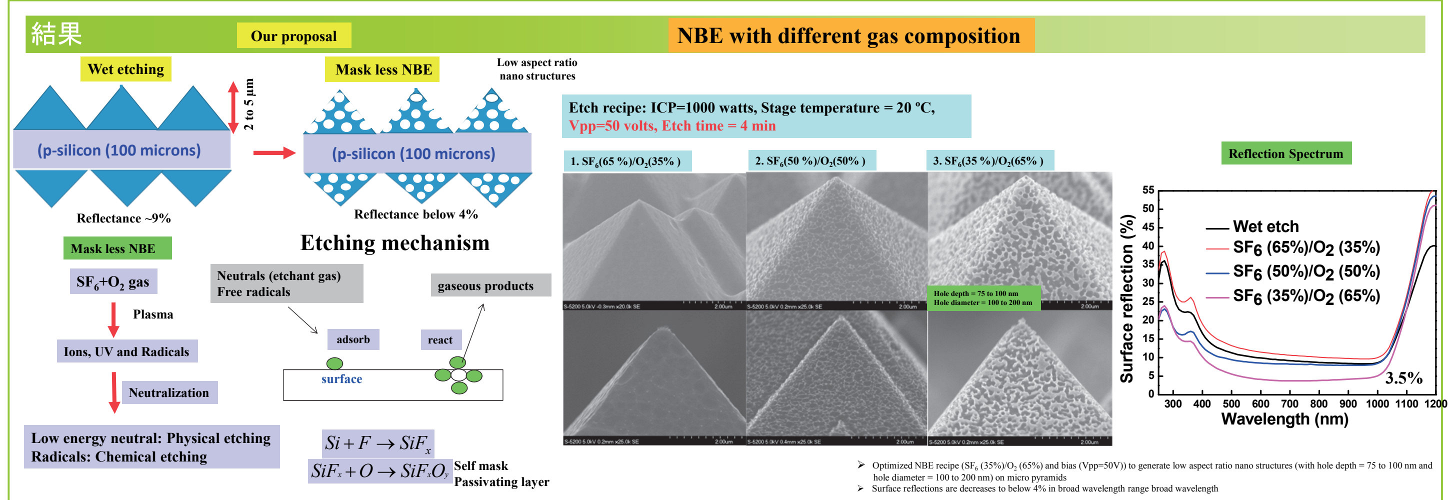

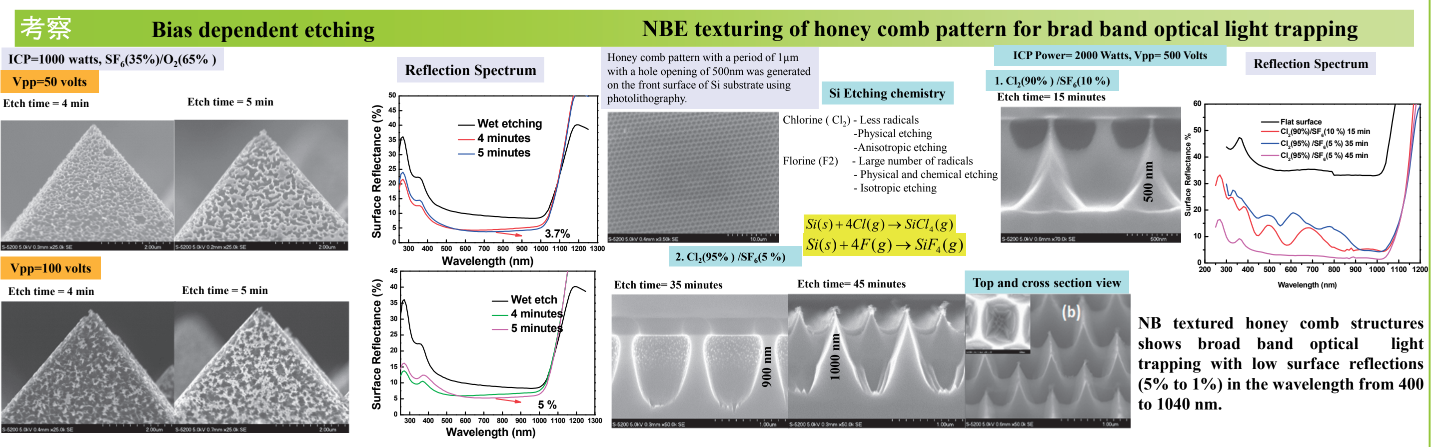

結論

- Introducing new innovative damage free (NBE) technology to trap the light in thin wafer based Si (<100 μm) solar cells.
- Nano holes with optimum etch depths (100 nm) on micro pyramids decreases surface reflections below 4% in broad wavelength range compare to their micro pyramids (9%).
- NBE applied to texture honey comb pattern.
- Using NBE, we achieve very low reflectance, 5% to 1% in the spectral range from 400nm to 1040 nm.

参考文献

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Thank you very much for kind attention